

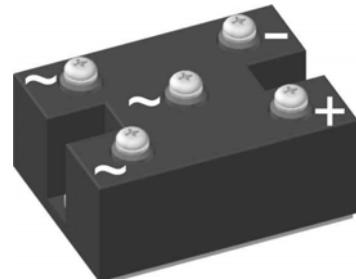
Standard Rectifier Module

3~ Rectifier
$V_{RRM} = 1400 \text{ V}$
$I_{DAV} = 150 \text{ A}$
$I_{FSM} = 1800 \text{ A}$

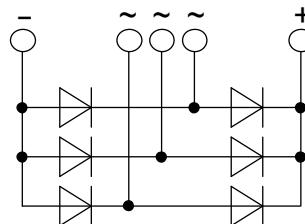
3~ Rectifier Bridge

Part number

VUO125-14NO7



 E72873



Features / Advantages:

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

Applications:

- Diode for main rectification
- For three phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

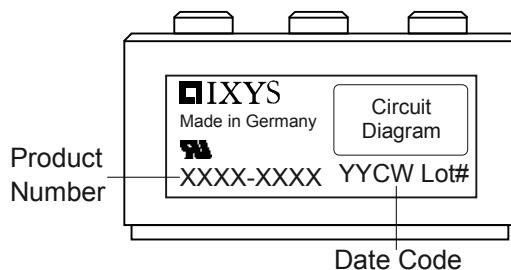
Package: PWS-C

- Industry standard outline
- RoHS compliant
- Easy to mount with two screws
- Base plate: Copper internally DCB isolated
- Advanced power cycling

Rectifier

Symbol	Definition	Conditions	Ratings			
			min.	typ.	max.	
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^\circ C$			1500	V
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^\circ C$			1400	V
I_R	reverse current	$V_R = 1400 V$ $V_R = 1400 V$	$T_{VJ} = 25^\circ C$ $T_{VJ} = 150^\circ C$		200 2	μA mA
V_F	forward voltage drop	$I_F = 50 A$ $I_F = 150 A$ $I_F = 50 A$ $I_F = 150 A$	$T_{VJ} = 25^\circ C$ $T_{VJ} = 125^\circ C$		1.07 1.34 0.97 1.31	V V
I_{DAV}	bridge output current	$T_C = 110^\circ C$ rectangular $d = \frac{1}{3}$	$T_{VJ} = 150^\circ C$		150	A
V_{FO} r_F	threshold voltage slope resistance } for power loss calculation only		$T_{VJ} = 150^\circ C$		0.76 3.6	V $m\Omega$
R_{thJC}	thermal resistance junction to case				0.6	K/W
R_{thCH}	thermal resistance case to heatsink			0.30		K/W
P_{tot}	total power dissipation		$T_C = 25^\circ C$		205	W
I_{FSM}	max. forward surge current	$t = 10 ms; (50 Hz)$, sine $t = 8,3 ms; (60 Hz)$, sine	$T_{VJ} = 45^\circ C$ $V_R = 0 V$		1.80 1.95	kA kA
		$t = 10 ms; (50 Hz)$, sine $t = 8,3 ms; (60 Hz)$, sine	$T_{VJ} = 150^\circ C$ $V_R = 0 V$		1.53 1.65	kA kA
I^2t	value for fusing	$t = 10 ms; (50 Hz)$, sine $t = 8,3 ms; (60 Hz)$, sine	$T_{VJ} = 45^\circ C$ $V_R = 0 V$		16.2 15.7	kA^2s kA^2s
		$t = 10 ms; (50 Hz)$, sine $t = 8,3 ms; (60 Hz)$, sine	$T_{VJ} = 150^\circ C$ $V_R = 0 V$		11.7 11.3	kA^2s kA^2s
C_J	junction capacitance	$V_R = 400 V; f = 1 MHz$	$T_{VJ} = 25^\circ C$	58		pF

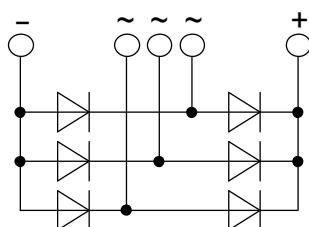
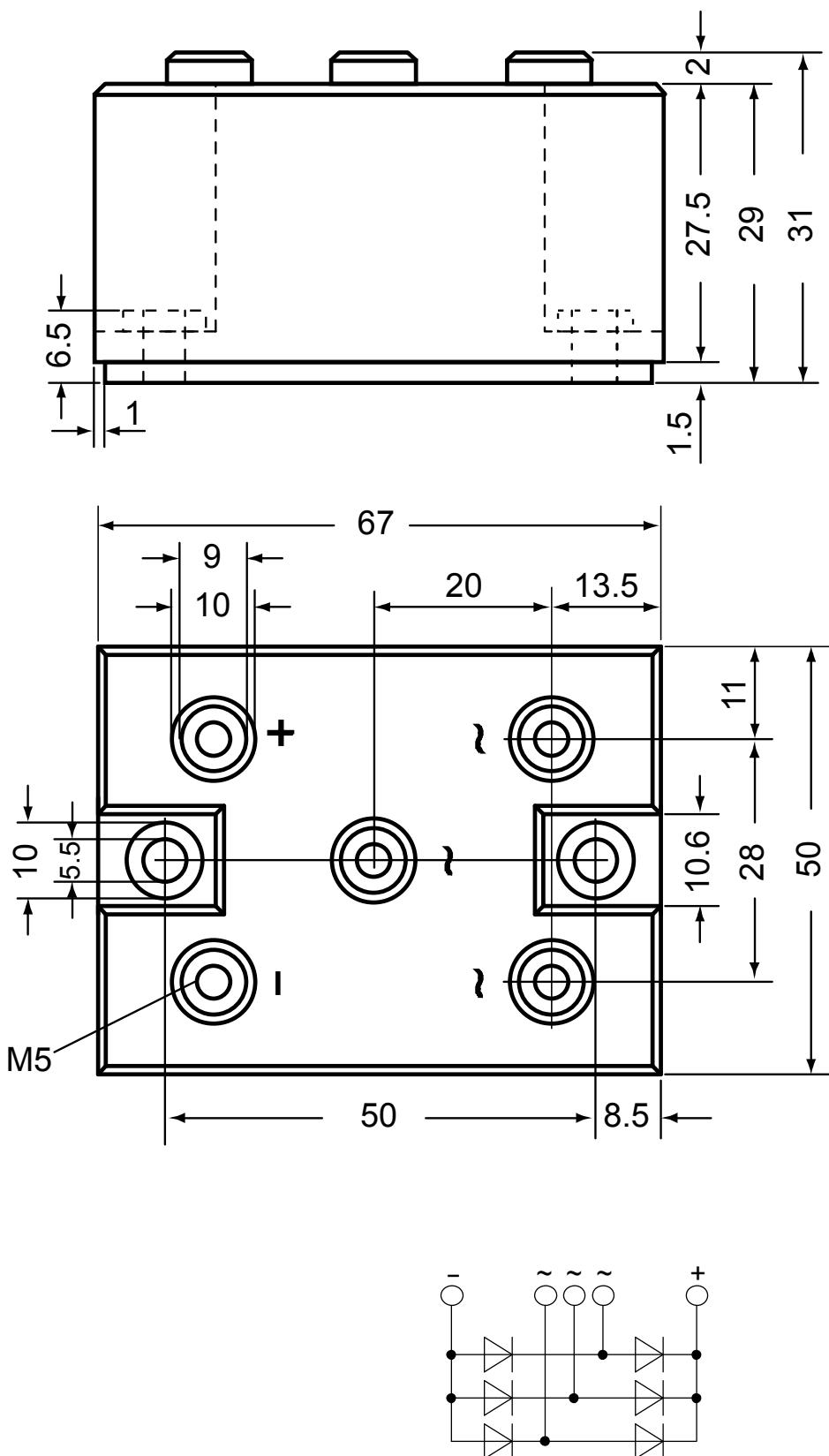
Package PWS-C			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			150	A
T_{stg}	storage temperature		-40		125	°C
T_{vJ}	virtual junction temperature		-40		150	°C
Weight				250		g
M_D	mounting torque		4.25		5.75	Nm
M_T	terminal torque		4.25		5.75	Nm
$d_{Spp/App}$	creepage distance on surface striking distance through air	terminal to terminal	26.0			mm
$d_{Spb/Abp}$		terminal to backside	14.0			mm
V_{ISOL}	isolation voltage	t = 1 second t = 1 minute	3000 50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA	2500		V V



Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	VUO125-14NO7	VUO125-14NO7	Box	10	456772

Equivalent Circuits for Simulation		* on die level	$T_{vJ} = 150$ °C
	Rectifier		
$V_{0\max}$	threshold voltage	0.76	V
$R_{0\max}$	slope resistance *	2.4	mΩ

Outlines PWS-C



Rectifier

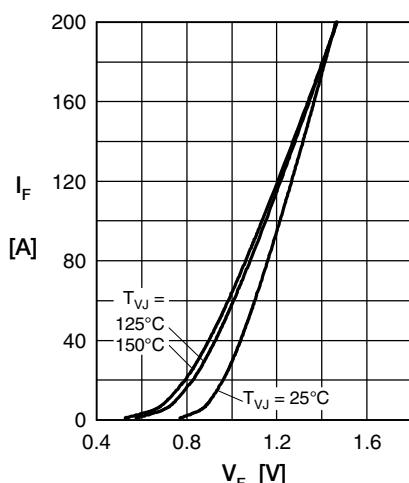


Fig. 1 Forward current versus voltage drop per diode

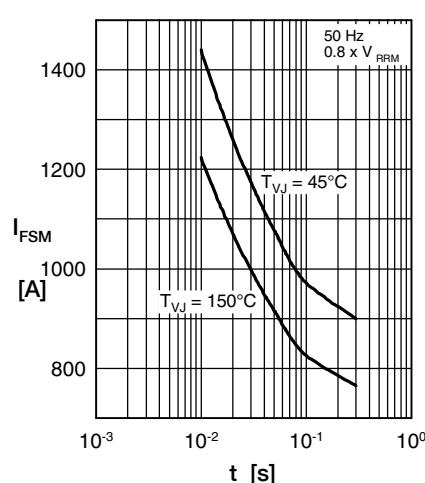


Fig. 2 Surge overload current vs. time per diode

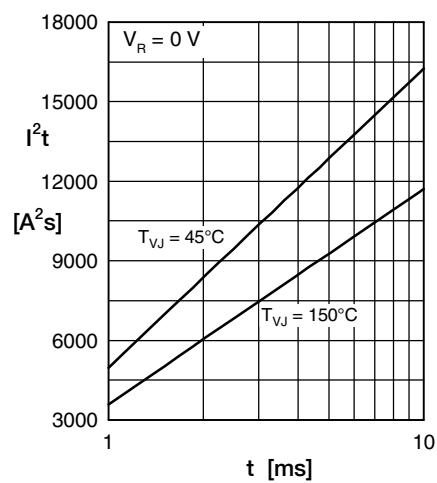
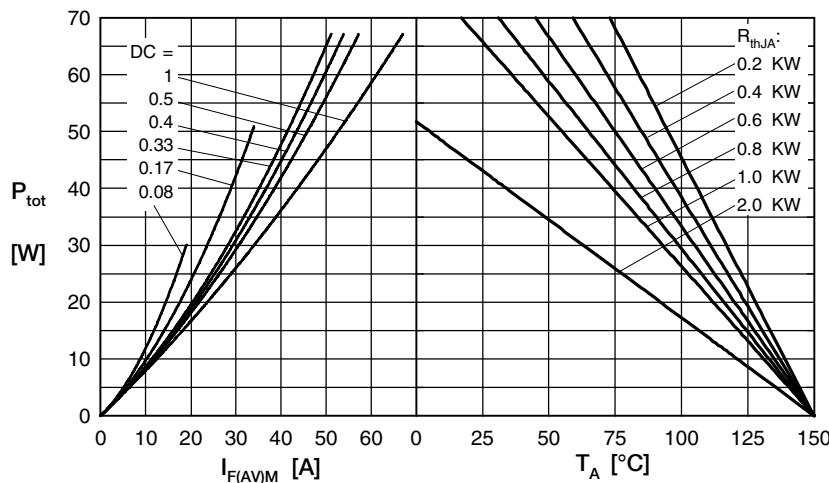
Fig. 3 I^2t versus time per diode

Fig. 4 Power dissipation vs. forward current and ambient temperature per diode

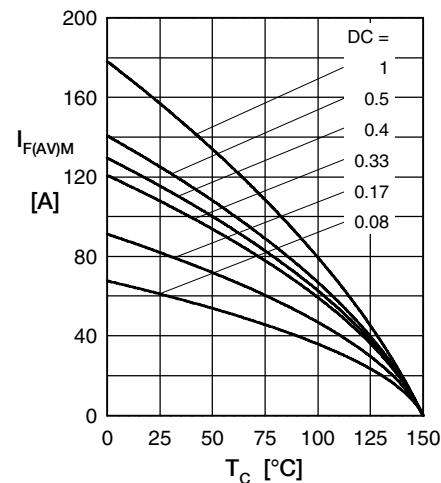


Fig. 5 Max. forward current vs. case temperature per diode

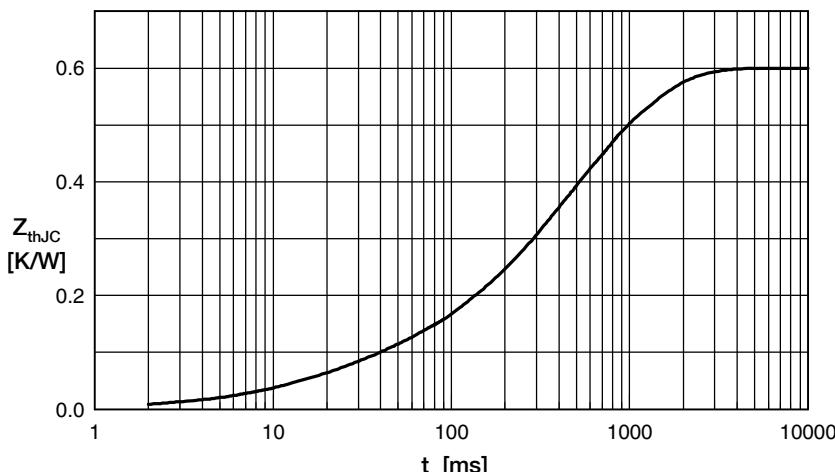


Fig. 6 Transient thermal impedance junction to case vs. time per diode

Constants for Z_{thJC} calculation:

i	R_{th} (K/W)	t_i (s)
1	0.060	0.020
2	0.003	0.010
3	0.150	0.225
4	0.243	0.800
5	0.144	0.580